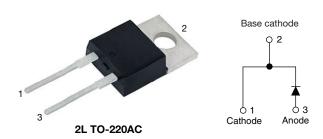


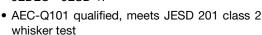
Hyperfast Rectifier, 30 A FRED Pt®



PRIMARY CHARACTERISTICS					
I _{F(AV)}	30 A				
V_{R}	650 V				
V _F at I _F	1.4 V				
t _{rr} typ.	33 ns				
T _J max.	175 °C				
Package	2L TO-220AC				
Circuit configuration	Single				

FEATURES

- · Hyper fast and soft recovery
- Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- True 2 pin package
- Designed and qualified according to JEDEC®-JESD 47



 Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





RoHS COMPLIANT

HALOGEN FREE Available

DESCRIPTION / APPLICATIONS

Ultra low V_F , soft-switching hyper fast rectifiers optimized for discontinuous (critical) mode (DCM) power factor correction (PFC).

The minimized conduction loss, optimized stored charge and low recovery current minimized the switching losses and reduce over dissipation in the switching element and snubbers.

The device is also intended for use as a freewheeling diode in power supplies and other power switching applications.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Repetitive peak reverse voltage	V_{RRM}		650	V			
Average rectified forward current	I _{F(AV)}	T _C = 120 °C	30				
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	210	A			
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	Ι _R = 100 μΑ	650	-	-		
Famous de la casa	V _F	I _F = 30 A	-	1.8	2.1	V	
Forward voltage		I _F = 30 A, T _J = 150 °C	-	1.4	1.6		
Devene leekene euwent		$V_R = V_R$ rated	-	0.02	30		
Reverse leakage current I _R		T _J = 150 °C, V _R = V _R rated	-	50	300	μΑ	
Junction capacitance	C _T	V _R = 650 V	-	22	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH	



DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Reverse recovery time t_{rr}	t	T _J = 25 °C	I _F = 1 A dI _F /dt = 100 A/μs V _R = 30 V	-	37	-	ns		
	trr	T _J = 25 °C		-	33	-	113		
		T _J = 125 °C			=	88	-		
Dook roomen ourrent		T _J = 25 °C	I _F = 30 A	=	18	-	Α		
Peak recovery current	IRRM	IRRM	IRRM	T _J = 125 °C	$dI_F/dt = 1000 A/\mu s$ $V_R = 400 V$	-	30	-	A
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	450	-	200		
		T _J = 125 °C		-	1350	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS (T _J = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, junction to case	R _{thJC}		-	1.0	1.3	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	70	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	-	0.5	
Maight			-	2.0	-	g
Weight			-	0.07	-	OZ.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style: 2L TO-220AC	ETH3007TH			

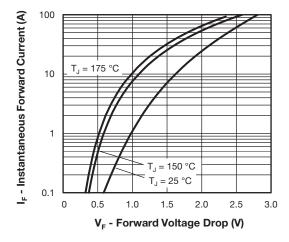


Fig. 1 - Typical Forward Voltage Drop Characteristics

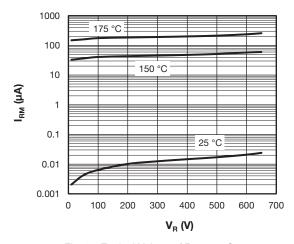


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



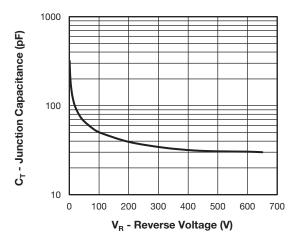


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

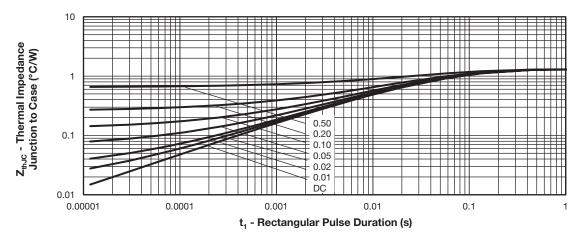


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

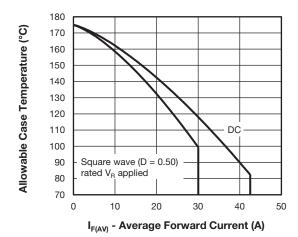


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

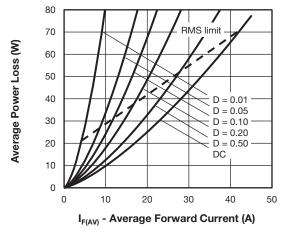


Fig. 6 - Forward Power Loss Characteristics

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; $Pd = forward power loss = I_{F(AV)} \times V_{FM} at (I_{F(AV)}/D)$ (see fig. 6); $Pd_{REV} = inverse power loss = V_{R1} \times I_R (1 - D)$; I_R at $V_{R1} = rated V_R$

www.vishay.com

Vishay Semiconductors

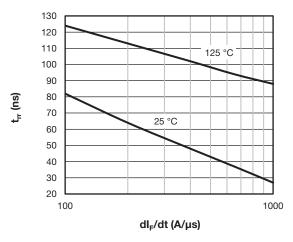


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

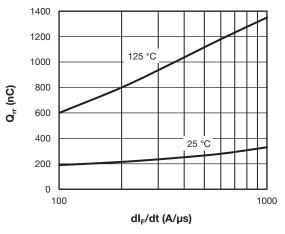
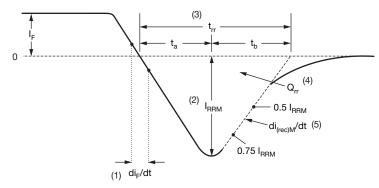


Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

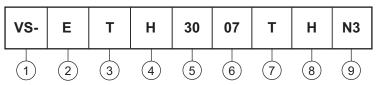
(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - E = single diode

- Package:

T = TO-220AC

- H = hyper fast recovery

5 - Current rating (30 = 30 A)

6 - Voltage rating (07 = 650 V)

7 - True 2 pin TO-220

8 - H = AEC-Q101 qualified

9 - Environmental digit:

N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

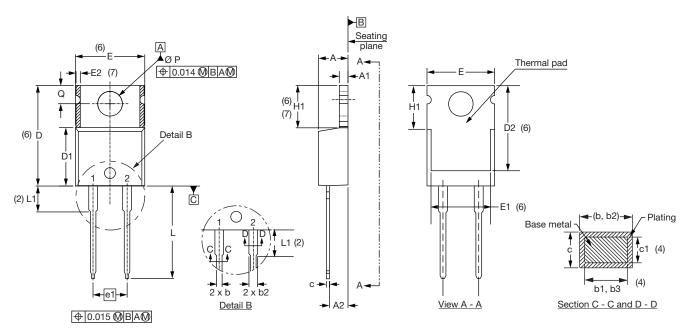
ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-ETH3007THN3	50	1000	Antistatic plastic tube			

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96069				
Part marking information	www.vishay.com/doc?95391				
SPICE model	www.vishay.com/doc?96531				



2L TO-220AC

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
E	10.11	10.51	0.398	0.414	3, 6

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E1	6.86	8.89	0.270	0.350	6
E2	1	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØP	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC® TO-220, except D2, where JEDEC® minimum is 0.480".



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.